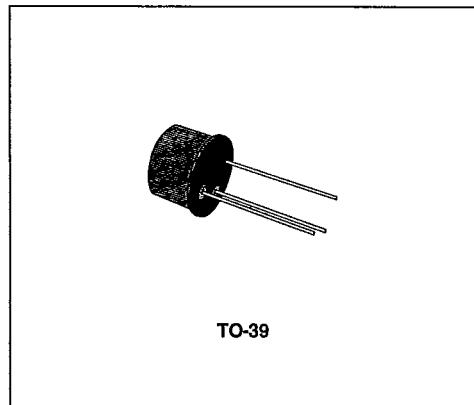
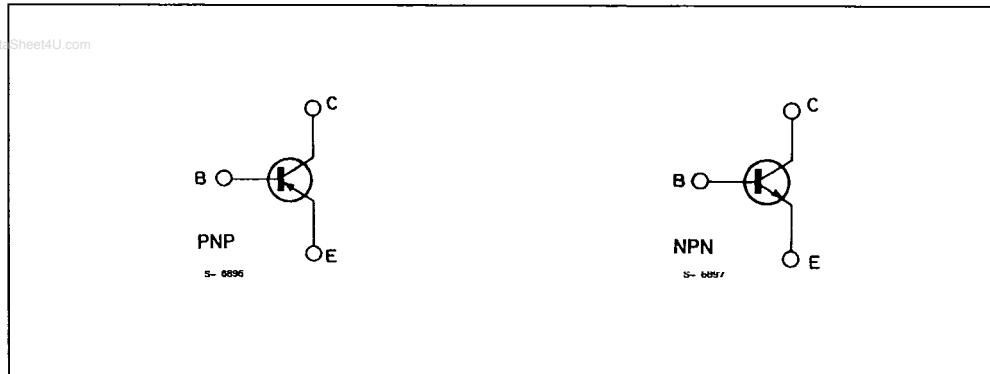


S G S-THOMSON
AUDIO AMPLIFIER
DESCRIPTION

The BC287 is a silicon planar epitaxial PNP transistor in Jedec TO-39 metal case. It is particularly intended for use as audio amplifier.

The complementary NPN type is the BC286.


INTERNAL SCHEMATIC DIAGRAM

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base Voltage ($I_E = 0$)	- 60	V
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	- 60	V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	- 5	V
I_C	Collector Current	- 1	A
P_{tot}	Total Power Dissipation at $T_{amb} \leq 25^\circ C$ at $T_{case} \leq 25^\circ C$	0.75 4	W W
T_{stg}, T_j	Storage and Junction Temperature	- 55 to 175	°C

THERMAL DATA

$R_{th\ j\text{-}case}$	Thermal Resistance Junction-case	Max	37	$^{\circ}\text{C}/\text{W}$
$R_{th\ j\text{-}amb}$	Thermal Resistance Junction-ambient	Max	200	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cutoff Current ($I_E = 0$)	$V_{CB} = -30\text{ V}$		0.1	50	nA
$V_{(BR)CBO}$	Collector-base Breakdown Voltage ($I_E = 0$)	$I_C = -10\text{ }\mu\text{A}$	-60			V
$V_{(BR)CEO}^*$	Collector-emitter Breakdown Voltage ($I_B = 0$)	$I_C = -10\text{ mA}$	-60			V
$V_{(BR)EBO}$	Emitter-base Breakdown Voltage ($I_C = 0$)	$I_E = -10\text{ }\mu\text{A}$	-5			V
$V_{CE(sat)}^*$	Collector-emitter Saturation Voltage	$I_C = -500\text{ mA } I_B = -50\text{ mA}$ $I_C = -1\text{ mA } I_B = -0.1\text{ mA}$		-0.25 -0.7	-1	V
V_{BE}^*	Base-emitter Voltage	$I_C = -500\text{ mA } V_{CE} = -2\text{ V}$		-0.93		V
h_{FE}^*	DC Current Gain	$I_C = -100\text{ mA } V_{CE} = -2\text{ V}$ $I_C = -500\text{ mA } V_{CE} = -2\text{ V}$	20	90 60		
f_T	Transition Frequency	$I_C = -50\text{ mA } V_{CE} = -5\text{ V}$ $f = 100\text{ MHz}$		150		MHz
C_{CBO}	Collector-base Capacitance ($I_E = 0$)	$V_{CB} = -10\text{ V}$ $f = 1\text{ MHz}$		13		pF

* Pulsed : pulse duration = 300 μs , duty cycle = 1 %.